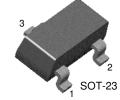


## KST55/56

### **Driver Transistor**

- Collector-Emitter Voltage: V<sub>CEO</sub> = KST55: 60V KST56: - 80V
- Collector Power Dissipation: P<sub>C</sub> (max) = 350mW
- Complement to KST05/06



1. Base 2. Emitter 3. Collector

## **PNP Epitaxial Silicon Transistor**

## **Absolute Maximum Ratings** $T_a$ =25°C unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector Base Voltage		
	: KST55	-60	V
	: KST56	-80	V
V <sub>CEO</sub>	Collector-Emitter Voltage		
	: KST55	-60	V
	: KST56	-80	V
V <sub>EBO</sub>	Emitter-Base Voltage	-4	V
I <sub>C</sub>	Collector Current	-500	mA
P <sub>C</sub>	Collector Power Dissipation	350	mW
T <sub>STG</sub>	Storage Temperature	150	°C
R <sub>TH</sub> (j-a)	Thermal Resistance junction to Ambient		°C/W

### Electrical Characteristics T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
BV <sub>CEO</sub>	* Collector-Emitter Breakdown Voltage : KST55	I <sub>C</sub> = -1mA, I <sub>B</sub> =0	-60		V
	: KST56	IC- 1111/14, IB-0	-80		v
BV <sub>EBO</sub>	* Emitter-Base Breakdown Voltage	I <sub>E</sub> = -100μA, I <sub>C</sub> =0	-4		V
I <sub>CBO</sub>	Collector Cut-off Current	V <sub>CB</sub> = -60V, I <sub>E</sub> =0		-0.1	μΑ
I <sub>CEO</sub>	Collector Cut-off Current				
	: KST55	$V_{CE} = -60V, I_{B} = 0$		-0.1	μΑ
	: KST56	V <sub>CE</sub> = -80V, I <sub>B</sub> =0		-0.1	μΑ
h <sub>FE</sub>	DC Current Gain	V <sub>CE</sub> = -1V, I <sub>C</sub> = -10mA	50		
		$V_{CE} = -1V, I_{C} = -100 \text{mA}$	50		
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -100mA, I <sub>B</sub> = -10mA		-0.25	V
V <sub>BE</sub> (on)	Base-Emitter On Voltage	V <sub>CE</sub> = -1V, I <sub>C</sub> = -100mA		-1.2	V
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> = -1V, I <sub>C</sub> = -100mA f=100MHz	50		MHz

<sup>\*</sup> Pulse Test: PW≤300μs, Duty Cycle≤2%

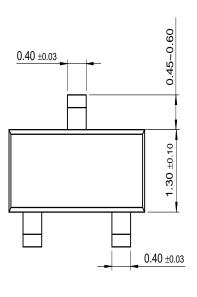
### **Marking Code**

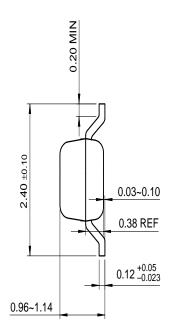
Туре	KST55	KST56
Mark	2H	2G

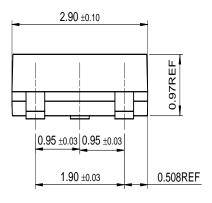


# **Package Dimensions**

# SOT-23







Dimensions in Millimeters

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CoolFET™	FASTr™	MicroFET™	PowerTrench <sup>®</sup>	SuperSOT™-6
CROSSVOLT™	FRFET™	MicroPak™	QFET™	SuperSOT™-8
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E <sup>2</sup> CMOS™	HiSeC™	MSXPro™	Quiet Series™	TruTranslation™
EnSigna™	$I^2C^{TM}$	OCXTM	RapidConfigure™	UHC™
Across the board.	. Around the world.™	OCXPro™	RapidConnect™	UltraFET®
The Power Franc	hise™	OPTOLOGIC <sup>®</sup>	SILENT SWITCHER®	VCX™
Programmable Ad	ctive Droop™	OPTOPLANAR™	SMART START™	

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Rev. I1

### **PRODUCT STATUS DEFINITIONS**

#### **Definition of Terms**

Datasheet Identification	Product Status	Definition
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